

## **isc Silicon NPN Power Transistors**

# BD375/377/379

#### **DESCRIPTION**

- DC Current Gain-
  - : h<sub>FE</sub>= 20(Min)@ I<sub>C</sub>= 1A
- Complement to Type BD376/378/380
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

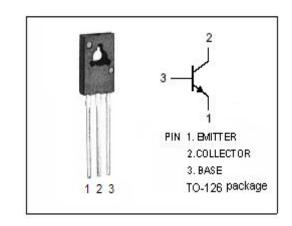
### **APPLICATIONS**

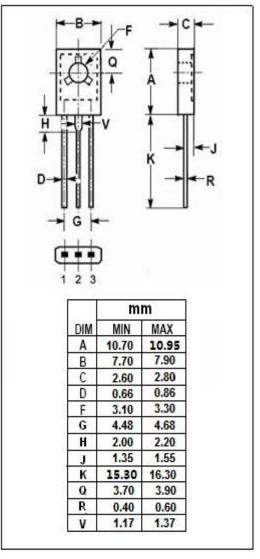
Designed for medium power linear and switching applications



ABSOLU	TE MAXIMUM RATINGS(Ta=25℃	')

SYMBOL	PARAMETER		VALUE	UNIT	
V <sub>СВО</sub>	Collector-Base Voltage	BD375	50		
		BD377	75	V	
		BD379	100		
		BD375	45		
$V_{\text{CEO}}$	Collector-Emitter Voltage	BD377	60	V	
		BD379	80		
V <sub>EBO</sub>	Emitter-Base Voltage	5	V		
Ic	Collector Current-Continuo	2	Α		
Ісм	Collector Current-Peak	3	Α		
I <sub>B</sub>	Base Current-Continuous	1	Α		
Pc	Collector Power Dissipatio @ T <sub>C</sub> =25°C	25	W		
TJ	Junction Temperature	150	$^{\circ}\!\mathbb{C}$		
T <sub>stg</sub>	Storage Temperature Rang	-55~150	$^{\circ}$		







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BD375/377/379

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	BD375	I <sub>C</sub> = 30mA ; I <sub>B</sub> = 0	45			
		BD377		60			V
		BD379		80			
	Collector-Base Voltage	BD375	I <sub>C</sub> = 0.1mA ; I <sub>E</sub> = 0	50			V
V <sub>СВО</sub>		BD377		75			
		BD379		100			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage		I <sub>C</sub> = 1A; I <sub>B</sub> = 0.1A			1.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage		I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V			1.5	V
		BD375	V <sub>CB</sub> = 45V; I <sub>E</sub> = 0			2	
І <sub>СВО</sub>	Collector Cutoff Current	BD377	V <sub>CB</sub> = 60V; I <sub>E</sub> = 0			2	μА
		BD379	V <sub>CB</sub> = 80V; I <sub>E</sub> = 0			2	
I <sub>EBO</sub>	Emitter Cutoff Current		V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			0.1	mA
h <sub>FE-1</sub>	DC Current Gain		I <sub>C</sub> = 0.15A; V <sub>CE</sub> = 2V	40		375	
h <sub>FE-2</sub>	DC Current Gain		I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V	20			
Switching T	Switching Times						
t <sub>on</sub>	Turn-On Time		I <sub>C</sub> = 0.5A; I <sub>B1</sub> = -I <sub>B2</sub> = 50mA;		0.05		μs
t <sub>off</sub>	Turn-Off Time		V <sub>CC</sub> = 30V		0.5		μs

### ♦ h<sub>FE-1</sub> Classifications

6	10	16	25
40-100	63-160	100-250	150-375

### **NOTICE:**

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